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May 2024

# FAN7621S PFM Controller for Half-Bridge Resonant Converters

#### **Features**

- Variable Frequency Control with 50% Duty Cycle for Half-bridge Resonant Converter Topology
- High Efficiency through Zero Voltage Switching (ZVS)
- Fixed Dead Time: 350ns
- Up to 300kHz Operating Frequency
- Auto-Restart Operation for All Protections with an External LV<sub>CC</sub>
- Protection Functions: Over-Voltage Protection (OVP), Over-Current Protection (OCP), Abnormal Over-Current Protection (AOCP), Internal Thermal Shutdown (TSD)

## **Applications**

- PDP and LCD TVs
- Desktop PCs and Servers
- Adapters
- Telecom Power Supraes
- Video Game Consol

## **Description**

The FAN7621S is a pulse framency modulation controller for high-efficiency nall- dge resonant converters. Offering everything necess by to build a reliable and robust resc ant con rter he FAN7621S Jductivity, while simplifies designs a im oves improving perform, ce. ⇒ FAN7621S includes a highside gate-drine circ that courante controlled oscillator free ency-limit coucit, soft-start, and built-in protection include. To high-side gate-drive circuit has mon ode use cancellation capability, which able of eration with excellent noise iar, tet. iı nur. Using the zero-voltage-switching (ZVS) tec iqu dramqually reduces to switching losses and sign, antly improves efficiency. The 2VS also reduces the switching hoise notherably, which allows a smallsized Electromagnetic Interference (EMI) filter.

The FAN7521S can be applied to various resonant converter topologies; such as series resonant, parallel resonant, and LLC reconant converters.

### Related Resources

AN4151 — Half-Bridge LLC Resonant Converter Design Using FSFR-Series Fairchild Power Switch (FPS<sup>TM</sup>)

## Oruring Information

	Part Number	Operating Junction	Package	Packaging Method
V	FAN7621SSJ	-40°C to +130°C	130°C 16-Lead, Small Outline Package (SOP)	
FAN7621SSJX		-40°C to +130°C	10-Leau, Siliali Outilile Fackage (SOF)	Tape & Reel

## **Application Circuit Diagram**

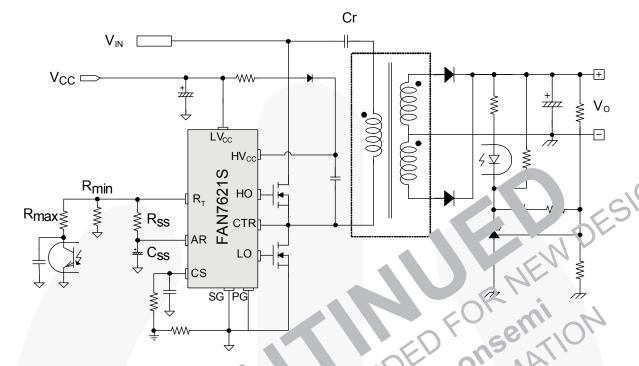
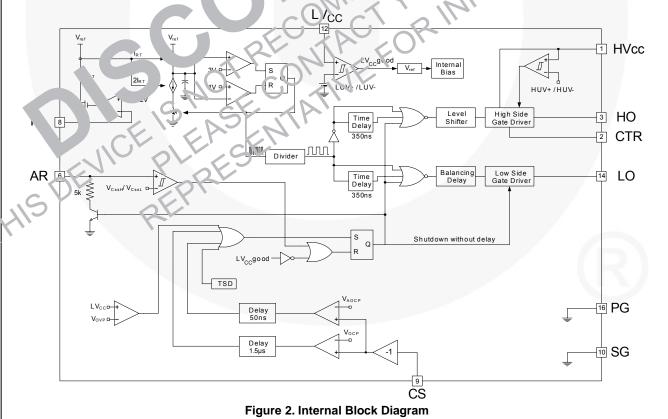
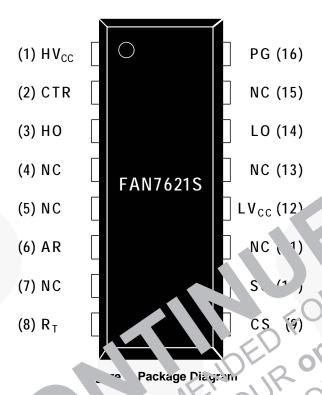


Figure 1. Typical Application Caracteristic Converted to the Converted Conve

## **Block Diagram**



## **Pin Configuration**



## **Pin Definitions**

Pin#	Description	
1	HV	This is a supply voltage of the high side gate-drive circuit IC.
2	;TR	ne drain of the low sign MOSFET. Typically, a transformer is connected to this pin.
3	но	This is the high-side, yate uriving signal.
	NC	No connection
5	١٧C	No connection
6	AP	This pin is for discharging the external soft-start capacitor when any protection is triggered. When the voltage or this pin drops to 0.2V, all protections are reset and the controller starts to operate again.
7	NC	No connection
8	R <sub>T</sub>	This pin programs the switching frequency. Typically, an opto-coupler is connected to control the switching frequency for the output voltage regulation.
9	CS	This pin senses the current flowing through the low-side MOSFET. Typically, negative voltage is applied on this pin.
10	SG	This pin is the control ground.
11	NC	No connection
12	LV <sub>CC</sub>	This pin is the supply voltage of the control IC.
13	NC	No connection
14	LO	This is the low-side gate driving signal.
15	NC	No connection
16	PG	This pin is the power ground. This pin is connected to the source of the low-side MOSFET.

## **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.  $T_A=25^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Min.	Max.	Unit
V <sub>HO</sub>	High-Side Gate Driving Voltage	V <sub>CTR</sub> -0.3	HV <sub>CC</sub>	V
$V_{LO}$	Low-Side Gate Driving Voltage	-0.3	$LV_CC$	V
LV <sub>CC</sub>	Low-Side Supply Voltage	-0.3	25.0	V
HV <sub>CC</sub> to V <sub>CTR</sub>	High-Side V <sub>CC</sub> Pin to Center Voltage	-0.3	25.0	V
$V_{CTR}$	Center Voltage	-0.3	\$	V
V <sub>AR</sub>	Auto-Restart Pin Input Voltage	-0.3	LV <sub>CC</sub>	V
V <sub>CS</sub>	Current Sense (CS) Pin Input Voltage	-5	0	V
V <sub>RT</sub>	R <sub>T</sub> Pin Input Voltage	<b>-</b> 0.	5.0	V
dV <sub>CTR</sub> /dt	Allowable Center Voltage Slew Rate		50	V/ns
P <sub>D</sub>	Total Power Dissipation		1.13	W
4	Maximum Junction Temperature <sup>(1)</sup>		+150	4.00
TJ	Recommended Operating Junction Temp atu (1)	-40	: (3)	°C C
T <sub>STG</sub>	Storage Temperature Range	-55	+150	) °C

#### Note:

1. The maximum value of the recommend the new new persons in temporature is limited by the mail shutdown.

## Thermal Impedan 3

Symbol	Parameter	Value	Unit
θ <sub>JA</sub> Juon-t	Ambient Thorn al Impedance	110	°C/W

## **Electrical Characteristics**

 $T_A \! = \! 25^{\circ} C$  and LV  $_{CC} \! = \! 17V$  unless otherwise specified.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Supply Sect	ion			I		
I <sub>LK</sub>	Offset Supply Leakage Current	HV <sub>CC</sub> =V <sub>CTR</sub>			50	μΑ
$I_QHV_{CC}$	Quiescent HV <sub>CC</sub> Supply Current	(HV <sub>CC</sub> UV+) - 0.1V		50	120	μA
I <sub>Q</sub> LV <sub>CC</sub>	Quiescent LV <sub>cc</sub> Supply Current	(LV <sub>CC</sub> UV+) - 0.1V		100	200	μA
I. UV	Operating HV <sub>CC</sub> Supply Current	f <sub>OSC</sub> =100kHz, C <sub>Load</sub> =1nF		5	8	mA
I <sub>O</sub> HV <sub>CC</sub>	(RMS Value)	No Switching		100	200	μA
$I_{O}LV_{CC}$	Operating LV <sub>cc</sub> Supply Current	f <sub>OSC</sub> =100kHz, C <sub>Load</sub> =1nF			9	mA
IOFACC	(RMS Value)	No Switching		2	4	mA
UVLO Section	on					
LV <sub>CC</sub> UV+	LV <sub>CC</sub> Supply Under-Voltage Positive-	Going Threshold (LV <sub>CC</sub> Start)	2	.2.5	13.8	V
LV <sub>CC</sub> UV-	LV <sub>CC</sub> Supply Under-Voltage Negative	e-Going Threshold (" V <sub>CC</sub> top)	8.5	10.0	11.1	V
LV <sub>CC</sub> UVH	LV <sub>CC</sub> Supply Under-Voltage Hysteres	is	2	2.5		V
HV <sub>CC</sub> UV+	HV <sub>CC</sub> Supply Under-Voltage Positive-Going Th. Sho. (Hv tart)			92	10.2	V
HV <sub>CC</sub> UV-	HVcc Supply Under-Voltage Negative	r Thre old IVcc Sίορ)	7.8	3.7	9.6	٧
HVccUVH	HV <sub>CC</sub> Supply Under-Voltage Hysternis			0.5		V
Oscillator &	Feedback Section	CNVIR	0	UH.		
$V_{RT}$	V-I Converter Three Jid Vunge	100	1.5	2.0	2.5	V
fosc	Output Oscillation F quency		94	100	106	kHz
DC	Output D / Cycle	J'C'AR"	48	50	52	%
f <sub>SS</sub>	I amal Sc Start litial Frequency	$f_{SS}=1_{OSC}+4C\kappa^{\mu}$ z, $F_{KT}=5.2k\Omega$		140		kHz
tss	In the ft-Start Time		2	3	4	ms
O'	n					
I <sub>source</sub>	Feak Sourcing Current	HV <sub>CC</sub> =17V	250	360		mA
	Priak Sinking Current	HV <sub>CC</sub> =17V	460	600		mA
tr	Rising Time:			65		ns
t <sub>f</sub>	Falling Time	C <sub>Load</sub> =1nF, HV <sub>CC</sub> =17V		35	W.	ns
SVHOH	High Leve' of Liigh-Side Gate Driving Signal (VHVCC-VHO)				1.0	V
$V_{HOL}$	Low Level of High-Side Gate Driving Signal	I <sub>O</sub> =20mA			0.6	V
$V_{LOH}$	High Level of High-Side Gate Driving Signal (V <sub>LVCC</sub> -V <sub>LO</sub> )	10-20IIIA			1.0	V
$V_{LOL}$	Low Level of High-Side Gate Driving Signal				0.6	٧

## **Electrical Characteristics** (Continued)

 $T_A$ =25°C and LV<sub>CC</sub>=17V unless otherwise specified.

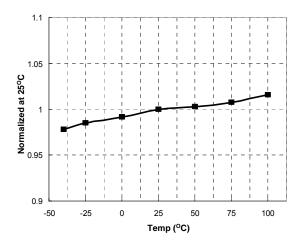
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit	
Protection Section							
V <sub>CssH</sub>	Beginning Voltage to Discharge C <sub>SS</sub>		0.9	1.0	1.1	V	
V <sub>CssL</sub>	Beginning Voltage to Charge C <sub>SS</sub> and Reset Protections		0.16	0.20	0.24	V	
$V_{OVP}$	LV <sub>CC</sub> Over-Voltage Protection	LV <sub>CC</sub> > 21V	21	23	25	V	
V <sub>AOCP</sub>	AOCP Threshold Voltage	ΔV/Δt=-0.1V/μs	-1.0	-0.9	-0.8	V	
t <sub>BAO</sub>	AOCP Blanking Time <sup>(2)</sup>	V <sub>CS</sub> < V <sub>AOCP</sub> ; ΔV/Δt=-0.1V/μs		50		ns	
$V_{OCP}$	OCP Threshold Voltage	ΔV/Δt=-1V/μs	0.6′	-0.	-0.52	٧	
t <sub>BO</sub>	OCP Blanking Time <sup>(2)</sup>	V <sub>CS</sub> < V <sub>OCP</sub> ; ΔV/Δt=-1V/μs		1.5	2.0	μs	
$t_{DA}$	Delay Time (Low-Side) Detecting from V <sub>AOCP</sub> to Switch Off <sup>(2)</sup>	ΔV/Δt=-1 <sup>2</sup>	OR	250	400	ns	
T <sub>SD</sub>	Thermal Shutdown Temperature <sup>(2)</sup>		110	13.1	150	°C	
Dead-Time	Dead-Time Control Section						
D <sub>T</sub>	Dead Time <sup>(3)</sup>	100	0,	350		ns	

#### Notes:

- These parameters, although g' rante 1, a not tested in production.
- 3. These parameters, although go arantee are lested only in EDS (wafer lest) process.

## **Typical Performance Characteristics**

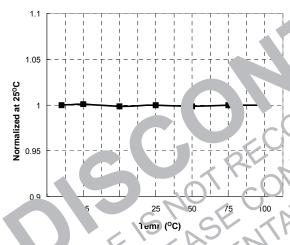
These characteristic graphs are normalized at T<sub>A</sub>=25°C.

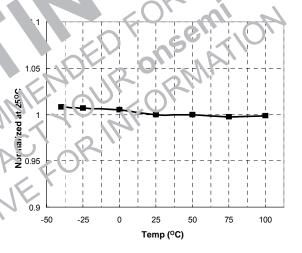


1.1 1.05 1.05 1.05 0.95 0.95 0.96 75 100

Figure 4. Low-Side MOSFET Duty Cycle vs. Temperature

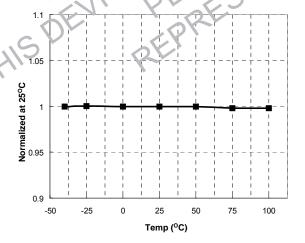
Figure 7. S. 'chin Frequency vs. Temperature





Figury Aigh-Side Vcc (HVc.) Start vs. Temperature

Figure 7. High-Side  $V_{CC}$  (HV<sub>CC</sub>) Stop vs. Temperature



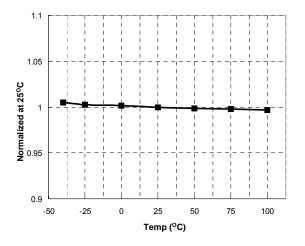
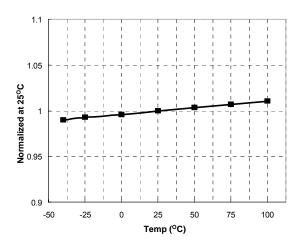


Figure 8. Low-Side V<sub>CC</sub> (LV<sub>CC</sub>) Start vs. Temperature

Figure 9. Low-Side  $V_{CC}$  (LV<sub>CC</sub>) Stop vs. Temperature

## **Typical Performance Characteristics** (Continued)

These characteristic graphs are normalized at T<sub>A</sub>=25°C.

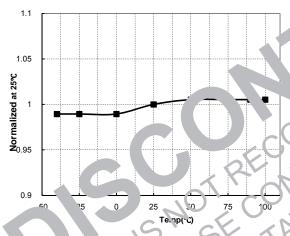


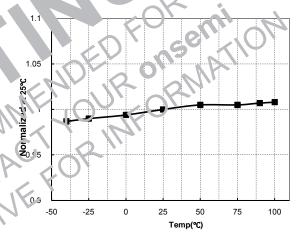
1.05 0.95 0.95 0.95 0.95 0.95 1.05 

1.1

Figure 10. LV $_{\text{CC}}$  OVP Voltage vs. Temperature

Fig re P oltage v.s. Temperature





igure 12. Voca vs. Temporature

Figure 13. V<sub>CssH</sub> vs. Temperature

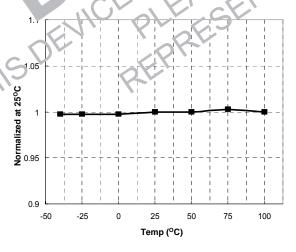


Figure 14. OCP Voltage vs. Temperature

## **Functional Description**

**1. Basic Operation**: FAN7621S is designed to drive high-side and low-side MOSFETs complementarily with 50% duty cycle. A fixed dead time of 350ns is introduced between consecutive transitions, as shown in Figure 15.

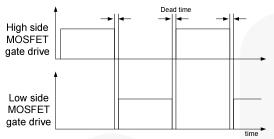


Figure 15. MOSFETs Gate Drive Signal

**2. Internal Oscillator**: FAN7621S employs a current-controlled oscillator, as shown in Figure 16. Internally, the voltage of  $R_T$  pin is regulated at 2V and the charging / discharging current for the oscillator capacitor,  $C_T$ , is obtained by copying the current flowing out of  $R_T$  pin ( $I_{CTC}$ ) using a current mirror. Therefore, the switch frequency increases as  $I_{CTC}$  increases.

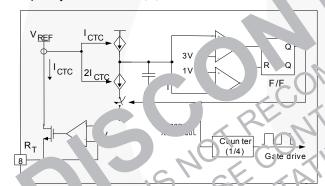


Fig. e 16. Current Controlled Oscillator

3. Frequency Setting: Figure 17 shows the typical voltage gain curve of a resonant converter, where the gain is inversely proportional to the switching frequency in the ZVS region. The cutput voltage can be regulated by modulating the switching frequency. Figure 18 shows the typical circuit configuration for  $R_T$  pin, where the optocoupler transistor is connected to the  $R_T$  pin to modulate the switching frequency.

The minimum switching frequency is determined as:

$$f^{\min} = \frac{5.2k\Omega}{R_{\min}} \times 100(kHz) \tag{1}$$

Assuming the saturation voltage of the opto-coupler transistor is 0.2V, the maximum switching frequency is determined as:

$$f^{\text{max}} = (\frac{5.2k\Omega}{R_{\text{min}}} + \frac{4.68k\Omega}{R_{\text{max}}}) \times 100(kHz)$$
 (2)

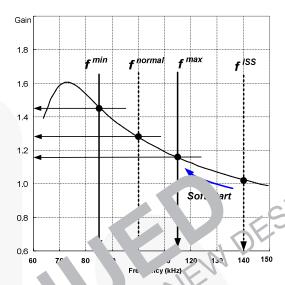


Figure 1 Re. nar Convertor Typical Gain Curve

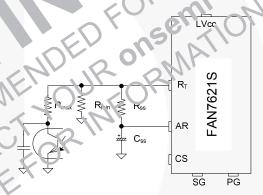


Figure 18. Frequency Control Circuit

To prevent excessive inrush current and overshoot of output voltage during startup, increase the voltage gain of the resonant converter progressively. Since the voltage gain of the resonant converter is inversely proportional to the switching frequency, the soft-start is implemented by sweeping down the switching frequency from an initial high frequency ( $f^{ISS}$ ) until the output voltage is established. The soft-start circuit is made by connecting R-C series network on the R<sub>T</sub> pin, as shown in Figure 18. FAN7621S also has an internal soft-start of 3ms to reduce the current overshoot during the initial cycles, which adds 40kHz to the initial frequency of the external soft-start circuit, as shown in Figure 19. The initial frequency of the soft-start is given as:

$$f^{ISS} = \left(\frac{5.2k\Omega}{R_{\min}} + \frac{5.2k\Omega}{R_{SS}}\right) \times 100 + 40 \ (kHz) \tag{3}$$

It is typical to set the initial (soft-start) frequency two  $\sim$  three times the resonant frequency ( $f_{\rm O}$ ) of the resonant network.

The soft-start time is three to four times the RC time constant. The RC time constant is as follows:

$$t_{SS} = R_{SS} \bullet C_{SS} \tag{4}$$

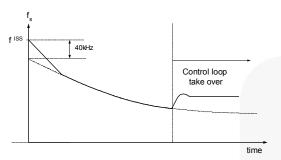


Figure 19. Frequency Sweeping of Soft-Start

**4. Self Auto-restart**: The FAN7621S can restart automatically even if a built-in protection is triggered with external supply voltage. As shown in Figure 20 and Figure 21; once any protections are triggered, M1 switch turns on and V-I converter is disabled.  $C_{\rm SS}$  starts to be discharged until the  $V_{\rm Css}$  across  $C_{\rm SS}$  drops to  $V_{\rm CssL}$ . Then all protections are reset, M1 turns off, and V-I converter resumes. The FAN7621S starts switching again with start. If the protections occur while  $V_{\rm CssL}$  is und  $V_{\rm CssL}$  and  $V_{\rm CssL}$  level, the switching is terminated immentely,  $V_{\rm Css}$  continues to increase until reaching  $V_{\rm CssL}$  is discharged by M1.

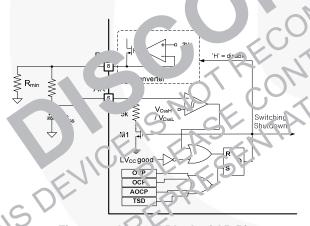


Figure 20. Internal Block of AR Pin

After protections trigger, FAN7621S is disabled during the stop-time,  $t_{\text{stop}}$ , where  $V_{\text{Css}}$  decreases and reaches to  $V_{\text{CssL}}$ . The stop-time of FAN7621S can be estimated as:

$$t_{stop} = C_{ss} \cdot \{ (R_{ss} + R_{min}) \parallel 5k\Omega \}$$
 (5)

For the soft-start time, t<sub>s/s</sub> it can be set as Equation (4).

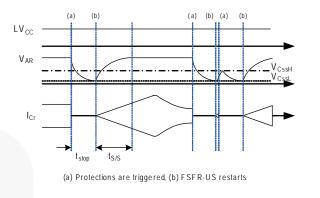


Figure 21. Self Auto-Restart Operation

**5. Protection Circuits**: The FA 621S as several self protective functions, such is er-Cu int Protection (OCP), Abnormal Over-Carent Procedure (AOCP), Over-Voltage Protection (OV 2 There is shutchown (TSD). These protections as a restrict mode protections, as shown in Fig. 3 21.

Once a fault cond on is detected, switching is ten and and consolers remain off. When LV<sub>CC</sub> alls upon stop voltage of 10V or the AR signal is Fig. , e protection is reset. FAN7 $\sigma^2$  is resumed normal operation, when LV<sub>CC</sub> reaches the scart voltage of 12.5V.

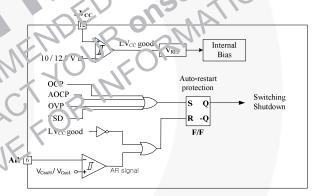


Figure 22. Protection Blocks

- **5.1 Over-Current Protection (OCP)**: When the sensing pin voltage drops below -0.58V, OCP is triggered and the MOSFETs remain off. This protection has a shutdown time delay of 1.5µs to prevent premature shutdown during startup.
- **5.2** Abnormal Over-Current Protection (AOCP): If the secondary rectifier diodes are shorted, large current with extremely high di/dt can flow through the MOSFET before OCP is triggered. AOCP is triggered without shutdown delay when the sensing pin voltage drops below -0.9V.
- **5.3 Over-Voltage Protection (OVP)**: When the LV<sub>CC</sub> reaches 23V, OVP is triggered. This protection is used when auxiliary winding of the transformer to supply  $V_{CC}$  to the controller is utilized.
- **5.4 Thermal Shutdown (TSD)**: If the temperature of the junction exceeds approximately 130°C, the thermal shutdown triggers.

**6. Current Sensing Using Resistor:** FAN7621S senses drain current as a negative voltage, as shown in Figure 23 and Figure 24. Half-wave sensing allows low power dissipation in the sensing resistor, while full-wave sensing has less switching noise in the sensing signal.

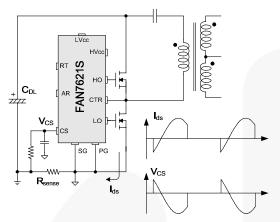
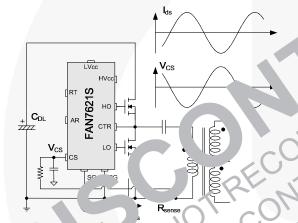
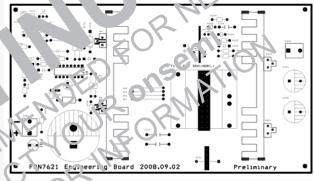


Figure 23. Half-Wave Sensing



F. vre 24. Fu'ii-Wave Sensing

7. PCB Layout Guidelines: Duty imbalance problems may occur due to the radiated noise from the main transformer, the inequality of the secondary-side leakage inductances of main transformer, and so on. It is one of the dominant reasons that the control components in the vicinity of R<sub>T</sub> pin are enclosed by the primary current flow pattern on PCB layout. The direction of the magnetic field on the components caused by the primary current flow is changed when the high- and low-side MOSFET turns on by turns. The magnetic fields with opposite direction from each other induce a current through, into, or out of the R<sub>T</sub> pin, which makes the turn-on duration of each MOSFET different. It is strongly recommended to separate the control components in the vicinity of R<sub>T</sub> pin from the primary current flow pattern on PCB layout. Error! Reference source not found. shows example for the duty-balanced case. The yellow nd blu 'ines show the primary current flows what the wer-s e and higher side MOSFETs turn or espe 'iver, T' primary current does not enclose and co nent of controller



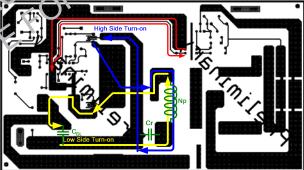
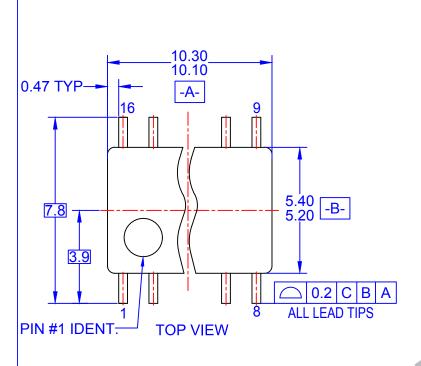
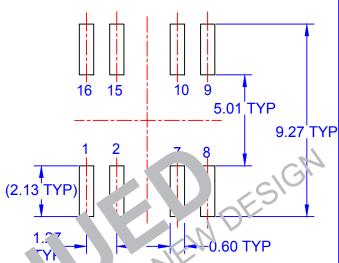
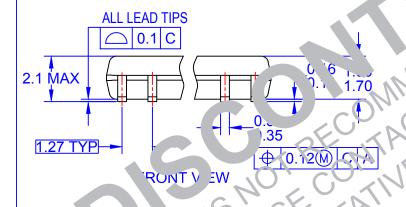


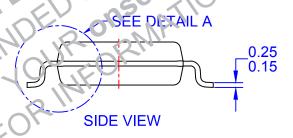
Figure 25. Example for Duty Balancing

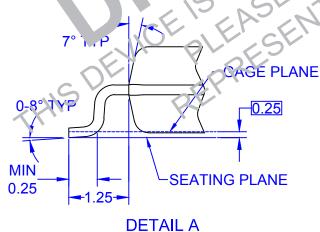




ATTERN RECOMMENDATION







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